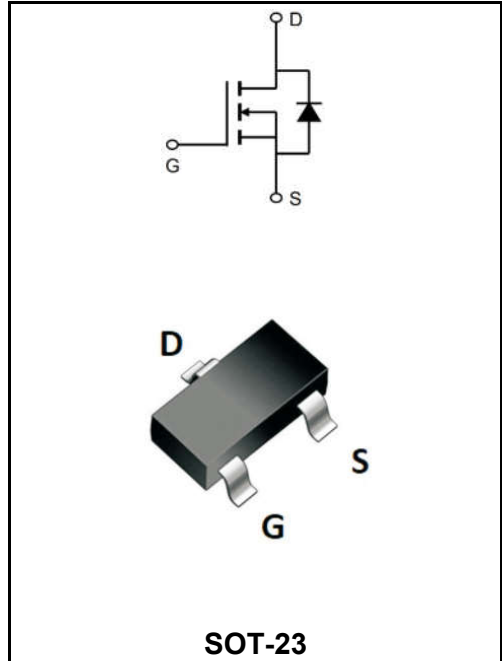


30V N-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

I_D	5.8A
V_{DSS}	30V
$R_{DS(on)-typ}(@V_{GS}=10V)$	< 38mΩ (Type:29 mΩ)



Application

- ◆ Lithium battery protection
- ◆ Wireless impact
- ◆ Mobile phone fast charging

Product Specification Classification

Part Number	Package	Marking	Pack
YFW3404B	SOT-23	3404B	3000PCS/Tape

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbols	Value	Units
Drain-Source Voltage	V_{DS}	30	V
Gate - Source Voltage	V_{GS}	±20	V
Continuous Drain Current $T_A=25^\circ\text{C}$	I_D	5.8	A
Continuous Drain Current $T_A=70^\circ\text{C}$	I_D	2.6	A
Pulsed Drain Current	I_{DM}	1.6	A
Power Dissipation $T_A = 25^\circ\text{C}$	P_D	1	W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	V(BR)DSS	30	32	-	V
Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V$	I_{DSS}	-	-	1.0	μA
Gate to Body Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	I_{GSS}	-	-	±100	nA
Gate -Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	V_{GS(th)}	1.2	1.5	2.5	V
Static Drain-Source on-Resistance note2	$V_{GS}=10V, I_D=4A$	R_{DS(ON)}	-	29	38	mΩ
	$V_{GS}=4.5V, I_D=3A$		-	45	65	
Input Capacitance	$V_{DS}=15V$ $V_{GS}=0V$ $f=1.0MHz$	C_{iss}	-	233	-	μF
Output Capacitance		C_{oss}	-	44	-	
Reverse Transfer Capacitance		C_{rss}	-	33	-	
Total Gate Charge	$V_{DS}=15V$ $V_{GS}=10V$ $I_D=2A$	Q_g	-	3	-	nC
Gate-Source Charge		Q_{gs}	-	0.5	-	
Gate-Drain("Miller") Charge		Q_{gd}	-	0.8	-	
Turn-on delay time	$V_{DS}=15V, I_D=4A,$ $R_{GEN}=3\Omega, V_{GS}=10V$	t_{d(on)}	-	4	-	ns
Turn-on Rise Time		T_r	-	2.1	-	
Turn-Off Delay Time		t_{d(OFF)}	-	15	-	
Turn-Off Fall Time		t_f	-	3.2	-	
Maximum Continuous Drain to Source Diode Forward Current		I_S	-	-	4	A
Maximum Pulsed Drain to Source Diode Forward Current		I_{SM}	-	-	16	A
Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=4A$	V_{SD}	-	-	1.2	V

Note :

- 1、 The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width $\cong 300\mu s$, duty cycle $\cong 2\%$
- 3、 The power dissipation is limited by 150°C junction temperature
- 4、 The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Ratings and Characteristic Curves

Typical Characteristics

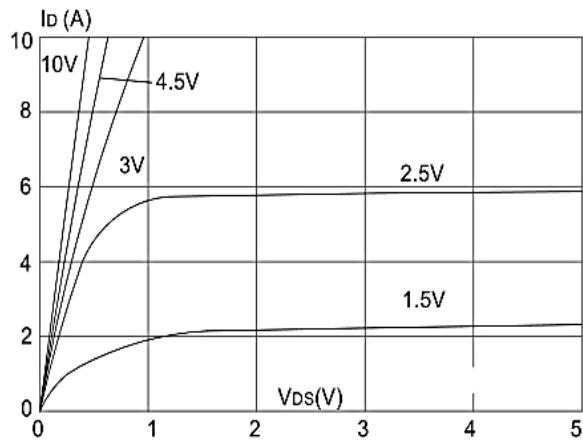


Figure 1: Output Characteristics

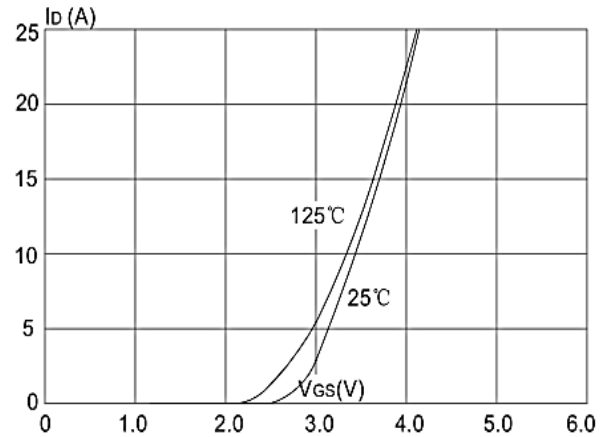


Figure 2: Typical Transfer Characteristics

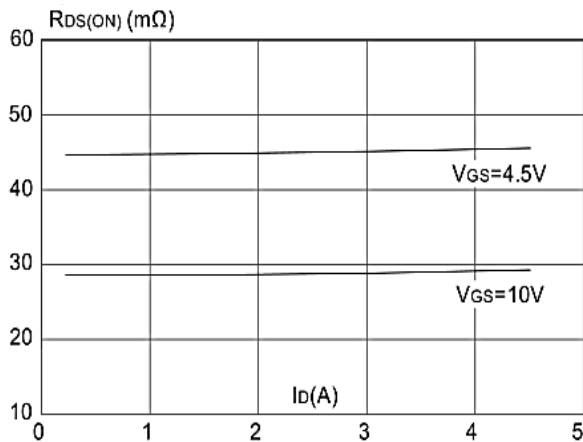


Figure 3: On-resistance vs. Drain Current

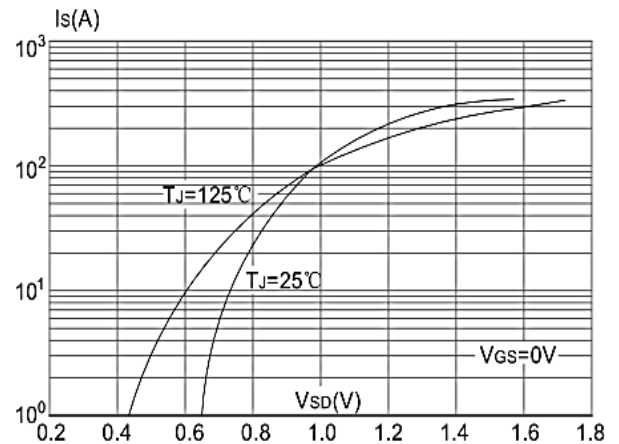


Figure 4: Body Diode Characteristics

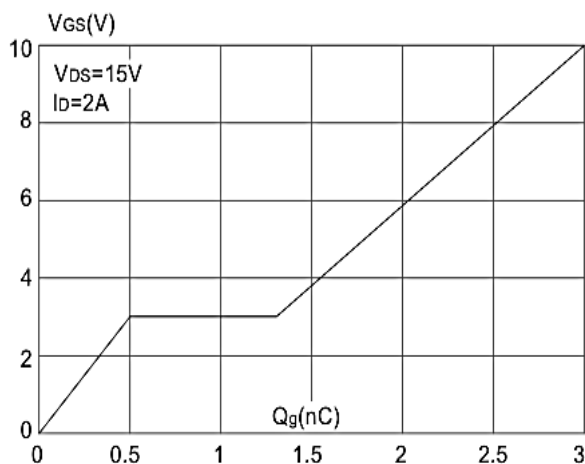


Figure 5: Gate Charge Characteristics

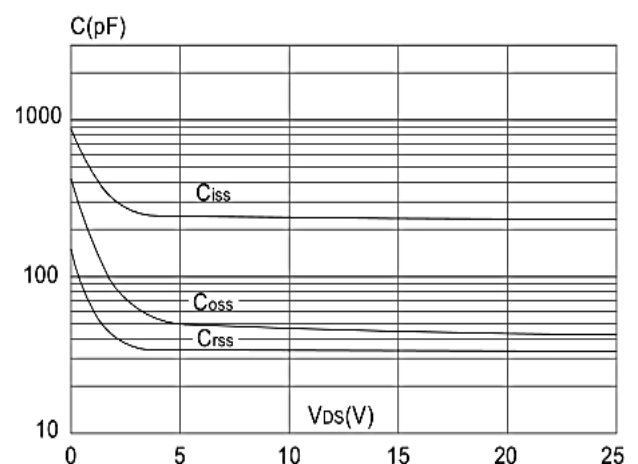


Figure 6: Capacitance Characteristics

Ratings and Characteristic Curves

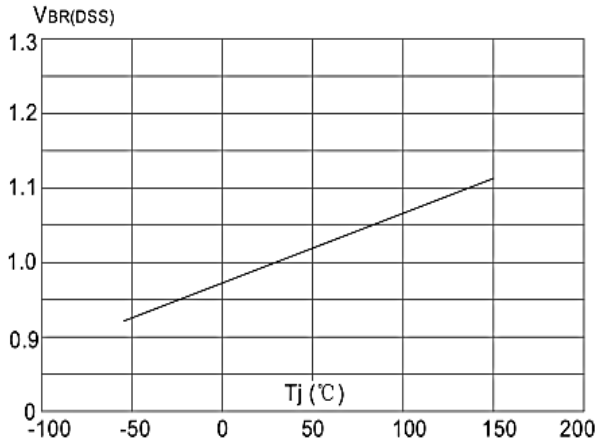


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

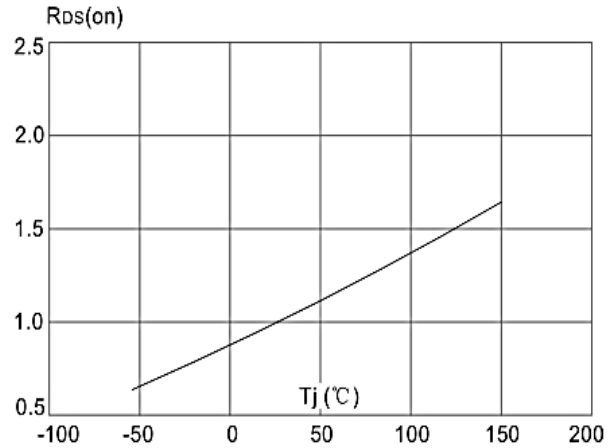


Figure 8: Normalized on Resistance vs. Junction Temperature

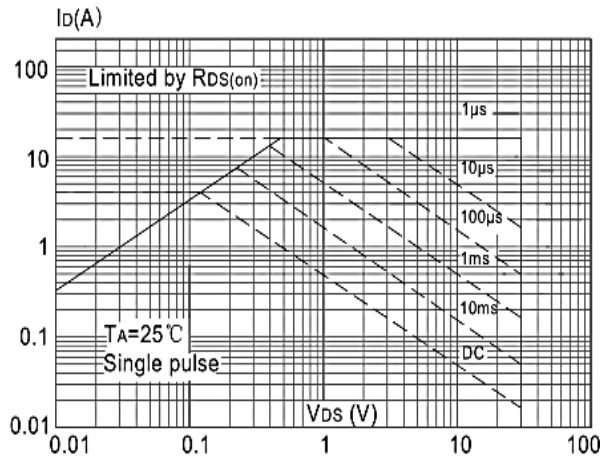


Figure 9: Maximum Safe Operating Area vs. Case Temperature

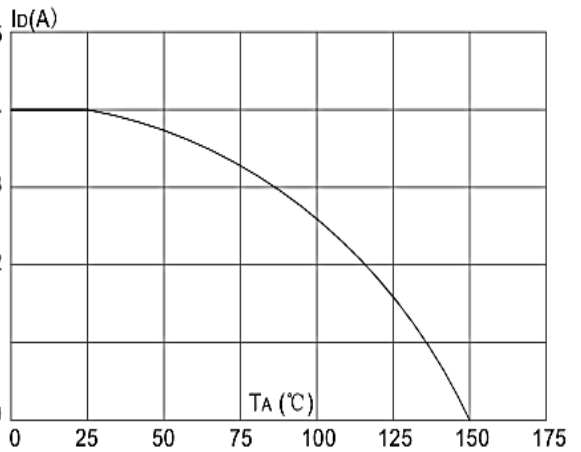


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

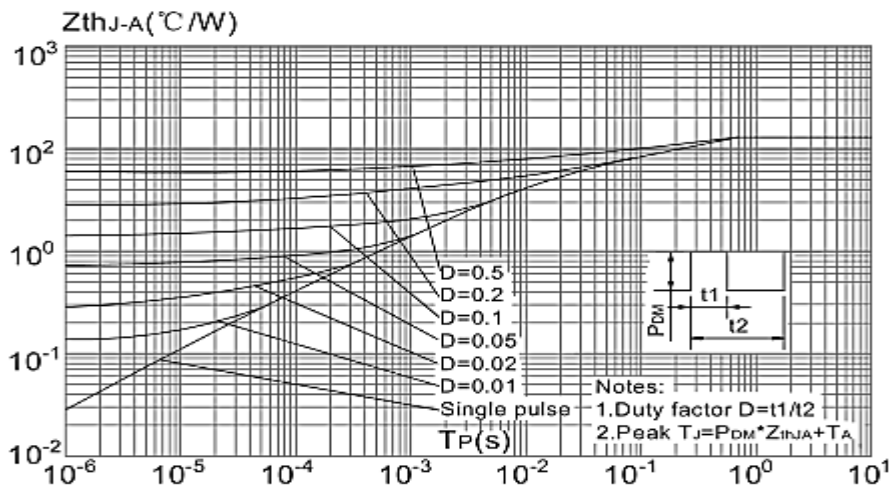
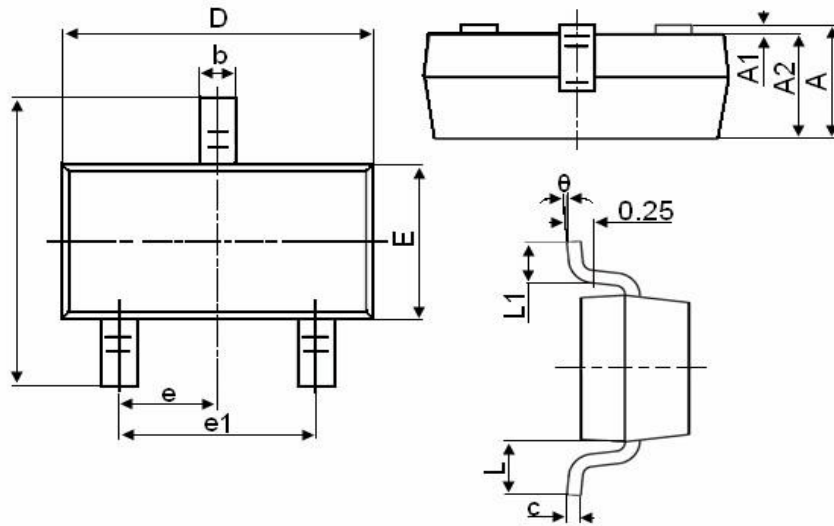


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

SOT-23



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

单击下面可查看定价，库存，交付和生命周期等信息

[>>YFW\(佑风微\)](#)